

SITAB74 Photo Interrupter

Dimensions (unit: mm)

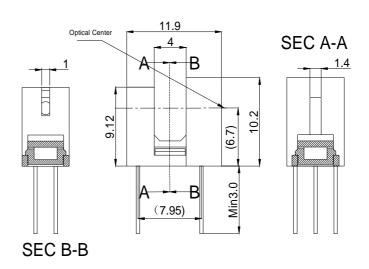
The SITAB74 consists of one infrared emitting diode facing two NPN silicon phototransistors encased in a black thermoplastic housing. Detector switching takes place whenever an opaque object passes through the slot between emitter and detector. The dual channels allow both the speed and the direction of the interrupter to be sensed.

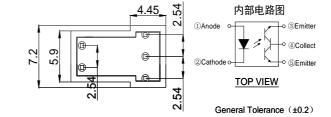
Features

- PCB mouning package
- · Gap:4mm
- Resolution:0.7mm
- · Rejection of ambient light
- RoHS Compliance

Applications

- Digital ammeter
- Disk drive





Maximum Ratings

/ T	$\alpha = 0$
112	-25°C\
110	=ノこ) しょ)

	Item	Symbol	Rating	Unit
	Power dissipation	P_{D}	75	mW
Input	Forward current	I _F	50	mA
	Reverse voltage	V_R	5	V
	Collector power dissipation	P _C	75	mW
Output	Collector current	Ic	20	mA
	Collector-Emitter voltage	V_{CEO}	30	V
	Emitter-Collector voltage	V _{ECO}	5	V
Operating	temperature *1	Topr.	-20 ~ +85	$^{\circ}$ C
Storage temperature *1		Tstg.	-30 ~ +85	$^{\circ}$ C
Soldering	temperature *2	Tsol.	260	$^{\circ}$ C

^{*1.} No icebond or dew

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^{*2.} The soldering should be 1.2mm away from bottom of the holder t=within 3s

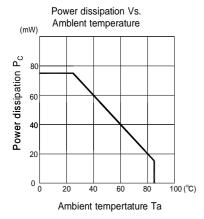
Photo Interrupter

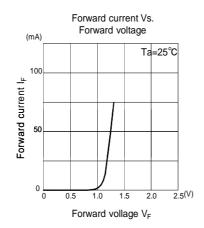
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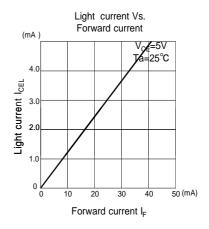
Elector-Optical Characteristics

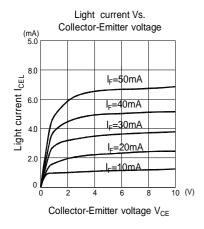
(Ta=25°C)

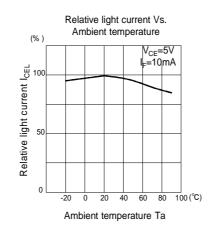
	Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input	Forward voltage	V_{F}	I _F =20mA		1.2	1.4	V
	Reverse current	I _R	V _R =5V	-	-	10	μΑ
	Peak wavelength	λ_{P}	I _F =20mA	-	940	-	nm
Output	Dark current	I _{CEO}	$V_{CE}=10V$ $E_{V}=0$ Ix	-	3	100	nA
	Peak SENS.Wavelength	λ_{P}	-	ı	880	-	nm
	Light current *3	I _{CEL}	I_F =5mA V_{CE} =5V Non-	0.3	-	3	mA
Transfer	Leak current *4	I_{CEOD}	I _F =5mA V _{CE} =5V Shading	ı	-	5	μΑ
charact- eristics	C-E sat.voltage	$V_{CE(sat)}$	$I_F=20$ mA $I_C=0.1$ mA	ı	0.2	0.4	V
	Rise time	tr	I_{C} =2mA V_{CC} =5V R_{I} =100 Ω	-	4	-	μs
	Fall time	tf	1C-21114 VCC-3V KL=100 12		5	-	μs

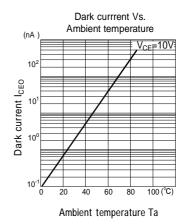








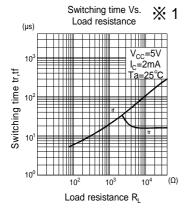


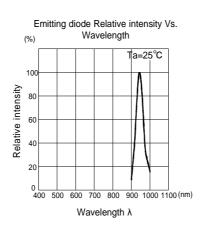


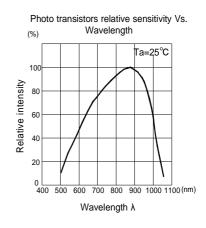
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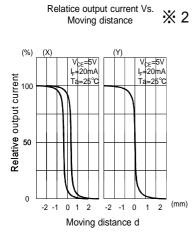
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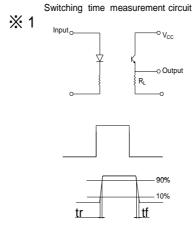
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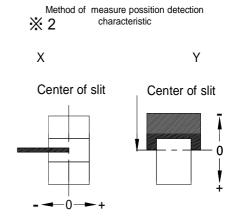
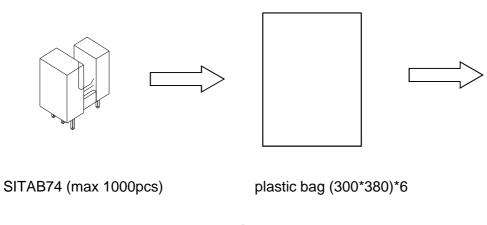


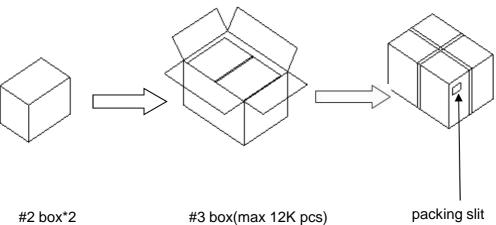
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SITAB74

Packing Specification

- 1.Fixed quantity (max 1000pcs) of the products are packed into plastic bag(300*380)
- 2.Six bags of the products are put into #2 box
- 3. Two #2 boxes are put into #3 box(max 12000pcs)
- 4. Packing slit is pasted on #3 box.





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